Graphite Crucible and Silicon Single Crystal Manufacturing Apparatus

Abstract

To provide a graphite crucible for silicon single crystal manufacturing according to the Czochralski method, wherein the graphite crucible has a long life cycle.

A characteristic resides in that at least one gas venting hole is provided in a corner portion of the crucible. A gas generated by a reaction between the graphite crucible and a quartz crucible is released to the outside through said at least one gas venting hole. Thereby, formation of SiC on the surface of the graphite crucible and deformation of the quartz crucible caused by the pressure of the gas are prevented.

Fig. 1